

ABSTRACT

There is provided a semiconductor device capable of improving the performance and reliability of a device. The semiconductor device includes comprising a gate structure including a gate electrode and a gate capping pattern on an upper surface of the gate electrode; a source/drain pattern on at least one side of the gate structure; and a source/drain contact on and connected with an upper surface of the source/drain pattern, the source/drain contact extending along a sidewall of the gate electrode, wherein an upper surface of the source/drain contact includes a convex curved surface.

FIG. 2a